



# STB80NF10

## N-CHANNEL 100V - 0.012Ω - 80A D2PAK LOW GATE CHARGE STripFET™ POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STB80NF10	100 V	< 0.015 Ω	80 A

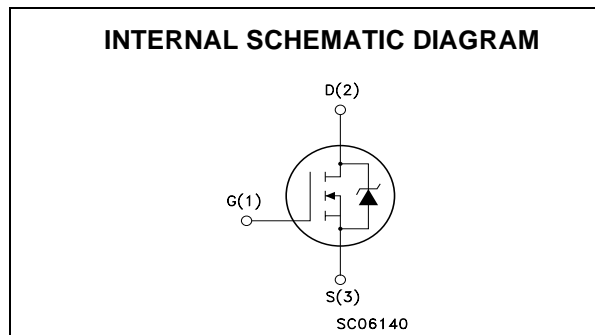
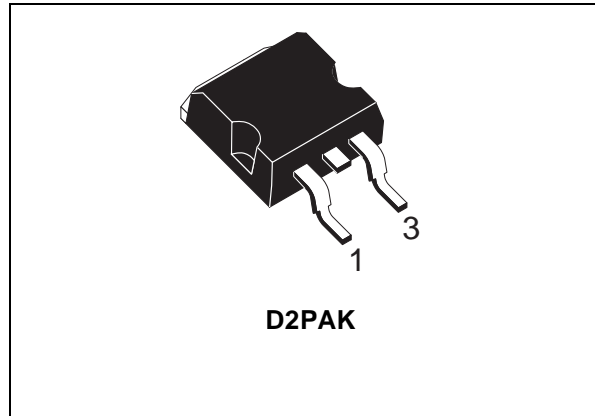
- TYPICAL R<sub>DS(on)</sub> = 0.012Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION

### DESCRIPTION

This Power MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency isolated DC-DC converters for Telecom and Computer application. It is also intended for any application with low gate charge drive requirements.

### APPLICATIONS

- HIGH-EFFICIENCY DC-DC CONVERTERS
- UPS AND MOTOR CONTROL



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	100	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	100	V
V <sub>GS</sub>	Gate- source Voltage	±20	V
I <sub>D</sub> (*)	Drain Current (continuous) at T <sub>C</sub> = 25°C	80	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	50	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	320	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	300	W
	Derating Factor	2	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	9	V/ns
E <sub>AS</sub> (2)	Single Pulse Avalanche Energy	245	mJ
T <sub>stg</sub>	Storage Temperature	-65 to 175	°C
T <sub>j</sub>	Max. Operating Junction Temperature	175	°C

(●) Pulse width limited by safe operating area

(\*) Limited by Package

(1) I<sub>SD</sub> ≤ 80A, di/dt ≤ 300A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

(2) Starting T<sub>j</sub> = 25°C, I<sub>D</sub> = 80A, V<sub>DD</sub> = 50V

## STB80NF10

### THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	0.5	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose	300	°C

### ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	100			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 40 A		0.012	0.015	Ω

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> , I <sub>D</sub> = 40 A		20		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		4300		pF
C <sub>oss</sub>	Output Capacitance			600		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			230		pF

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 50V, I_D = 40A$		40		ns
$t_r$	Rise Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		145		ns
$Q_g$	Total Gate Charge	$V_{DD} = 80V, I_D = 80A,$ $V_{GS} = 10V$		140	189	nC
$Q_{gs}$	Gate-Source Charge			23		nC
$Q_{gd}$	Gate-Drain Charge			51		nC

**SWITCHING OFF**

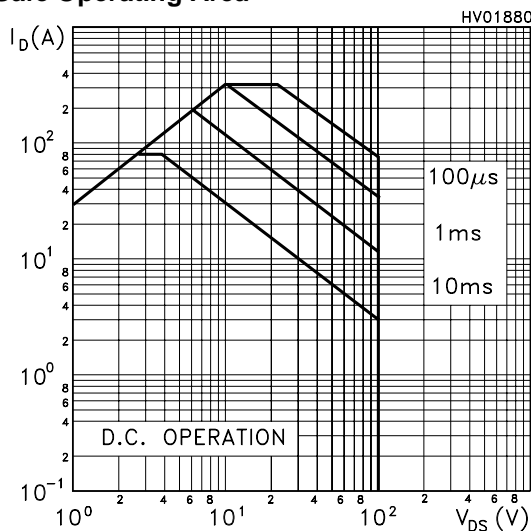
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 50V, I_D = 40A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		134		ns
$t_f$	Fall Time			115		ns
$t_{d(off)}$	Off-voltage Rise Time	$V_{clamp} = 80V, I_D = 80A$ $R_G = 4.7\Omega, V_{GS} = 10V$		111		ns
$t_f$	Fall Time	(see test circuit, Figure 5)		125		ns
$t_c$	Cross-over Time			185		ns

**SOURCE DRAIN DIODE**

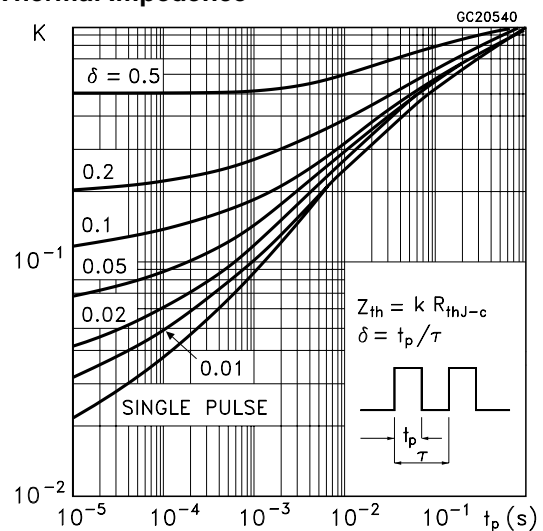
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				80	A
$I_{SDM(1)}$	Source-drain Current (pulsed)				320	A
$V_{SD(2)}$	Forward On Voltage	$I_{SD} = 80A, V_{GS} = 0$			1.3	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 80A, di/dt = 100A/\mu s,$ $V_{DD} = 50V, T_j = 150^\circ C$ (see test circuit, Figure 5)		155		ns
$Q_{rr}$	Reverse Recovery Charge					
$I_{RRM}$	Reverse Recovery Current					

Note: 1. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

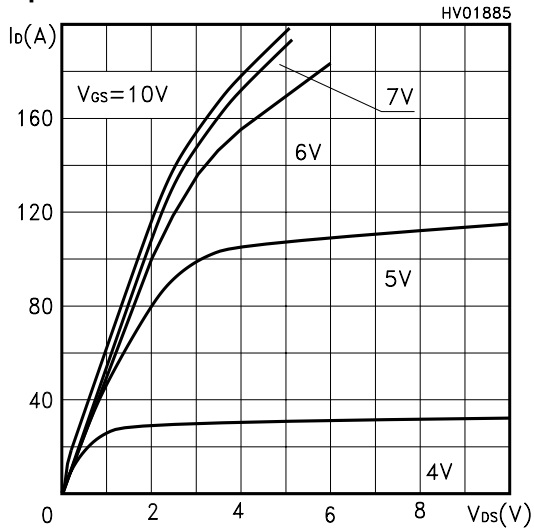
**Safe Operating Area**



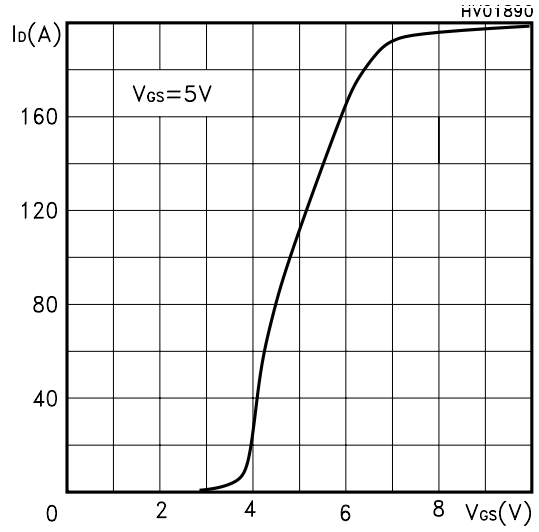
**Thermal Impedance**



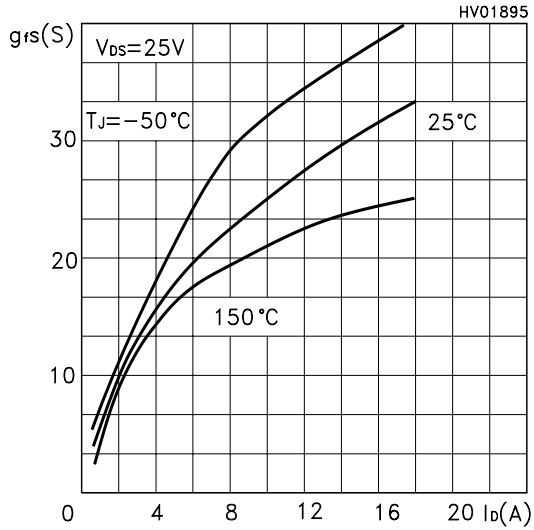
Output Characteristics



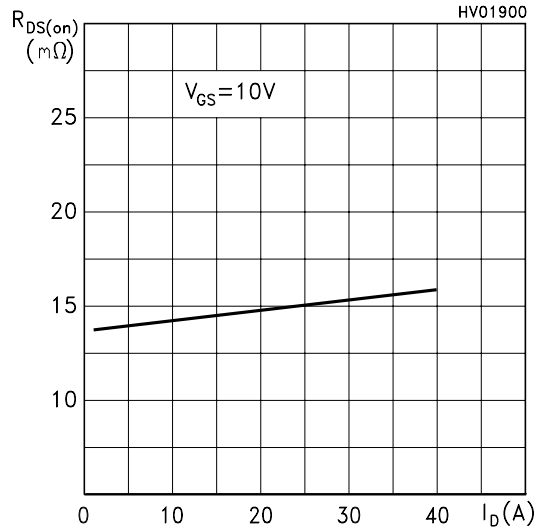
Transfer Characteristics



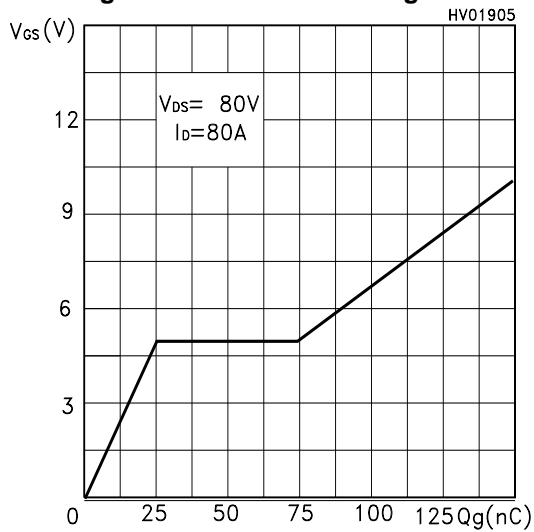
Transconductance



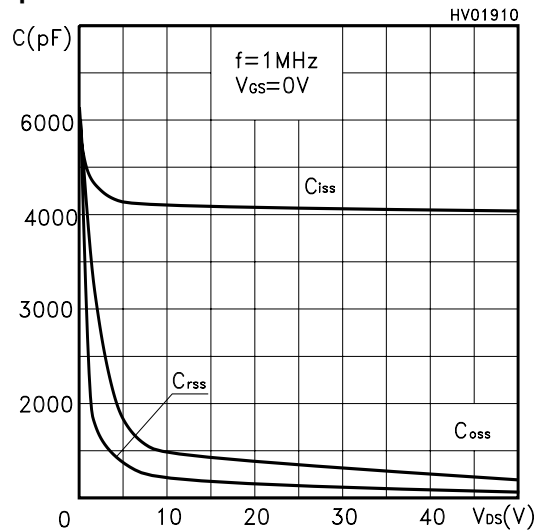
Static Drain-source On Resistance



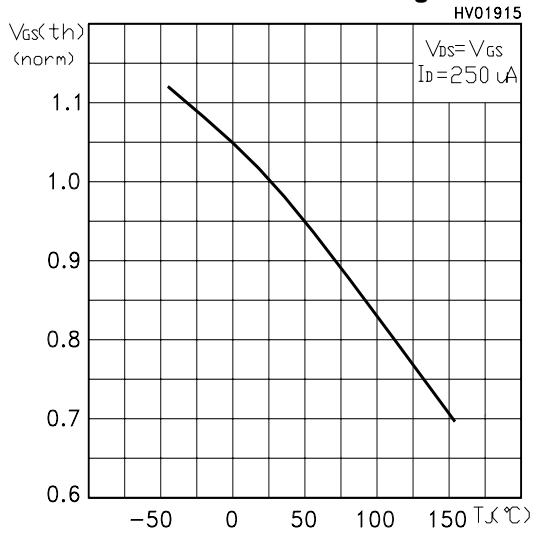
Gate Charge vs Gate-source Voltage



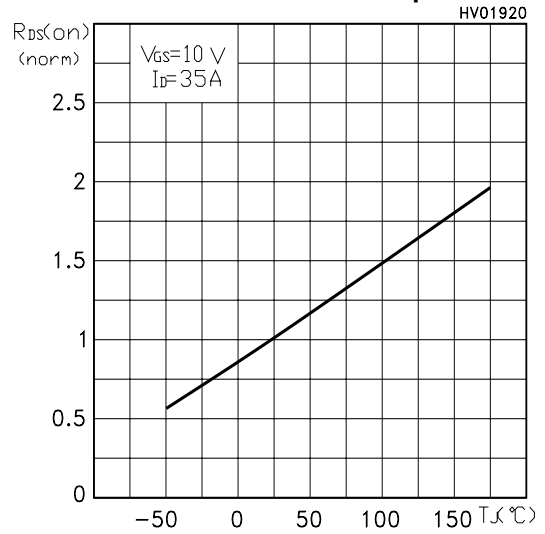
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

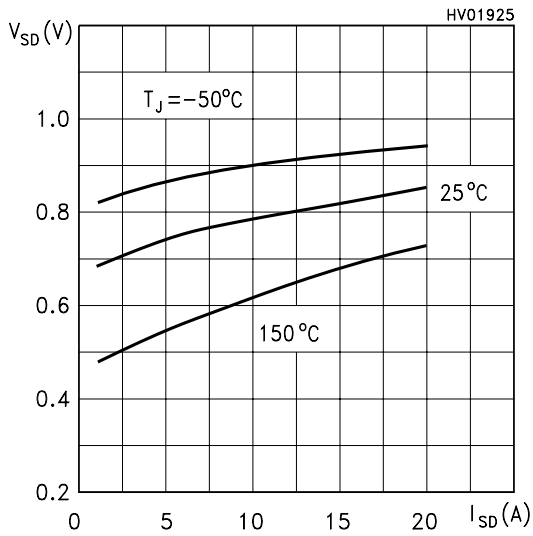


Fig. 1: Unclamped Inductive Load Test Circuit

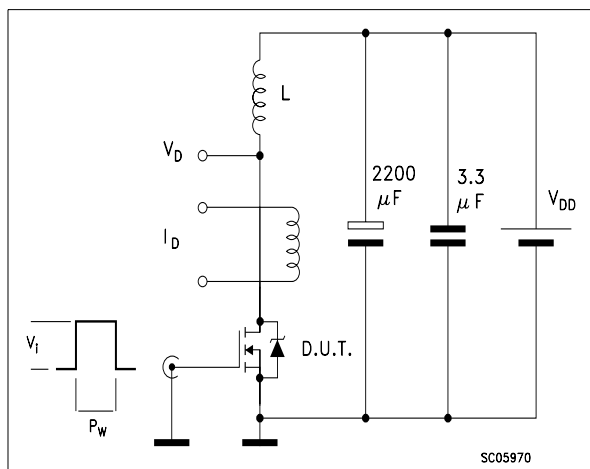


Fig. 2: Unclamped Inductive Waveform

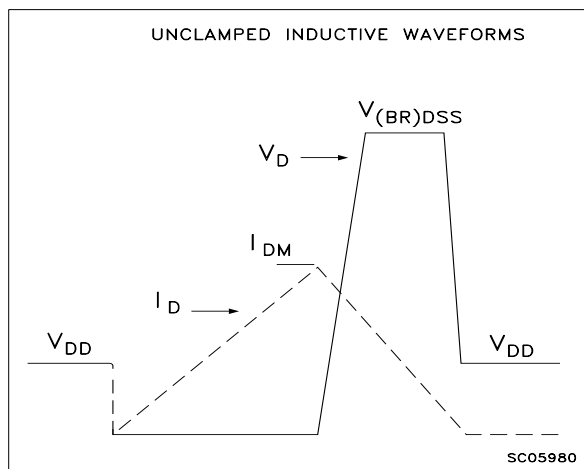


Fig. 3: Switching Times Test Circuit For Resistive Load

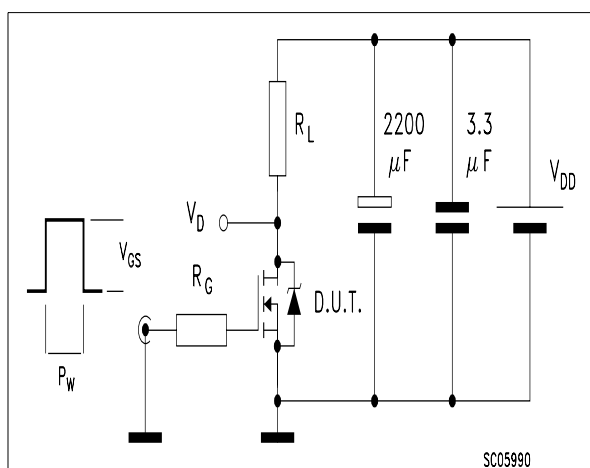


Fig. 4: Gate Charge test Circuit

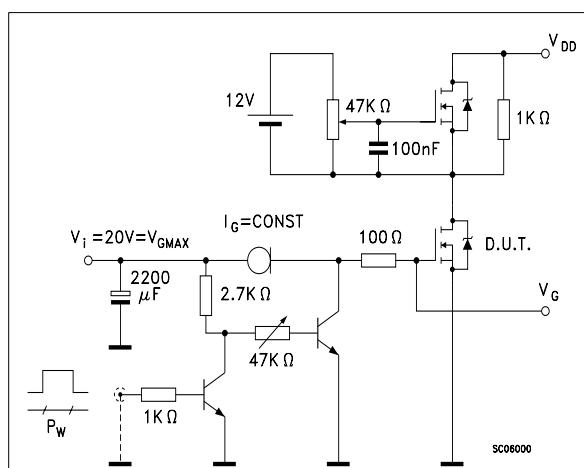
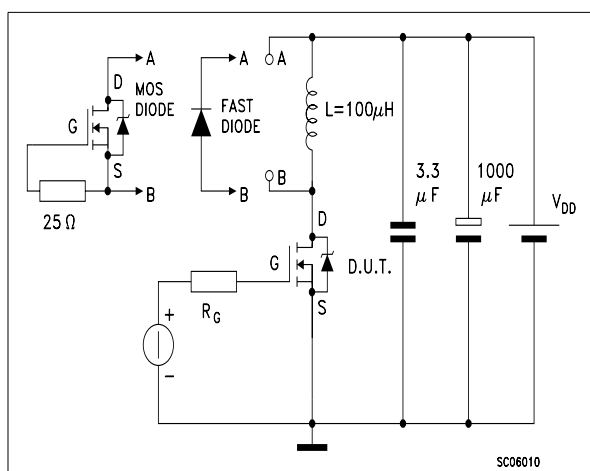
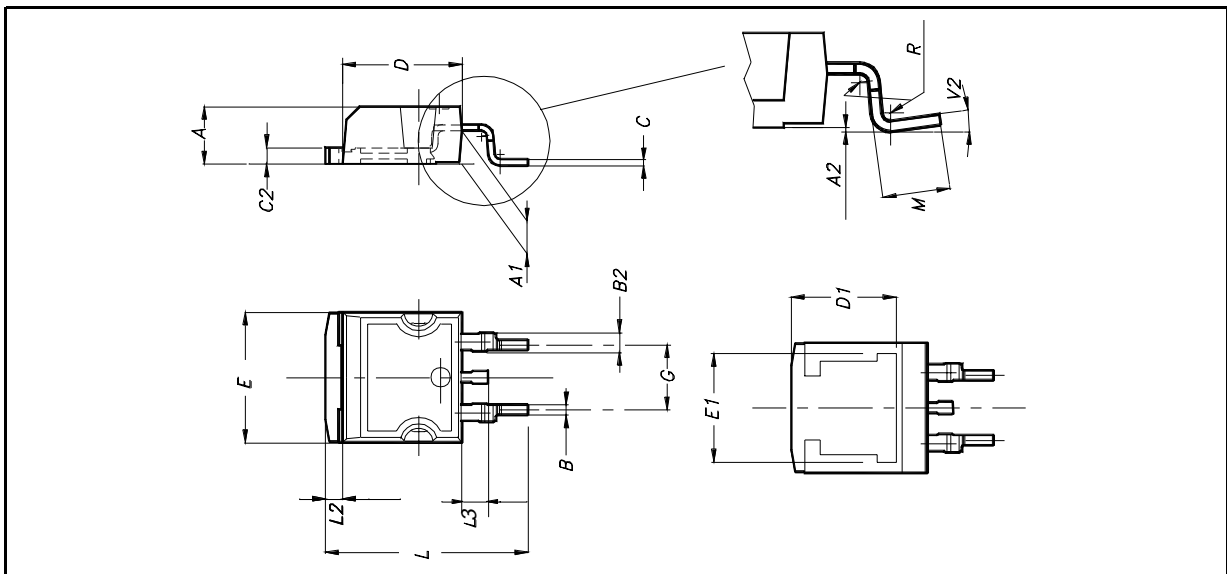


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



### D<sup>2</sup>PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°			



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